

ABSTRACT OF THE DISCLOSURE

A semiconductor memory is formed of first, second, third, fourth, fifth and sixth field effect transistors. The first and second transistors have a first line as gates, one ends of current paths of the first and second transistors are connected to a reference potential electrode. The third and fourth transistors have a second line as gates, and one ends of current paths of the third and fourth transistors are connected to the reference electrode. The fifth transistor has a first word line as a gate, and one end of a current path of the fifth transistor is connected to the other ends of the current paths of the first and second transistors. The sixth transistor having a second word line as a gate, and one end of a current path of the sixth transistor is connected to the other ends of the current paths of the third and fourth transistors.